AMENDMENTS TO THE CLAIMS:

1. (Currently amended) A field effect transistor, comprising:

a substrate comprising a source region, a drain region, and a channel region ~~therebetween~~ between said source region and said drain region;

B1 an insulating layer disposed over said channel region, said insulating layer comprising a layer comprising aluminum nitride and at least one of a layer of aluminum oxide, a layer of silicon dioxide, and a layer of silicon nitride disposed over said channel region; and

a gate electrode disposed over said insulating layer.

2. (Currently amended) The transistor of claim 1, wherein said layer of aluminum oxide is disposed upon said channel region, and wherein said layer of aluminum nitride is disposed over said aluminum oxide.

3. (Currently amended) The transistor of claim 1, wherein said layer of aluminum oxide is disposed over said channel region, and wherein said layer of aluminum nitride is disposed under said aluminum oxide.

4. (Currently amended) The transistor of claim 1, wherein said layer of silicon dioxide is disposed upon said channel region, and wherein said layer of aluminum nitride is disposed over said silicon dioxide.

5. (Currently amended) The transistor of claim 1, wherein said layer of silicon dioxide is disposed over said channel region, and wherein said layer of aluminum nitride is disposed under said silicon dioxide.

6. (Currently amended) The transistor of claim 1, wherein said layer of silicon nitride is disposed upon said channel region, and wherein said layer of aluminum nitride is disposed over said silicon nitride.

B1

7. (Currently amended) The transistor of claim 1, wherein said layer of silicon nitride is disposed over said channel region, and wherein said layer of aluminum nitride is disposed under said silicon nitride.

Claims 8-13. (Currently canceled)

14. (Currently amended) A field effect transistor, comprising:

a substrate comprising a source region, a drain region, and a channel region between said source region and said drain region ~~therebetween~~;

an insulating layer disposed over said channel region, said insulating layer comprising a first layer comprising aluminum oxide disposed upon said channel region and a second layer comprising aluminum nitride disposed upon said first layer; and

a gate electrode disposed over said insulating layer.

15. (Currently amended) A semiconductor device, comprising:

a substrate comprising a source region, a drain region, and a channel region ~~therebetween~~ between said source region and said channel region;

an insulating layer disposed over said channel region, said insulating layer comprising a layer comprising aluminum nitride and a layer comprising at least one of aluminum oxide, silicon dioxide, and silicon nitride ~~disposed over said channel region~~; and

a gate electrode disposed over said insulating layer.

16. (Original) The semiconductor device of claim 15, wherein said device comprises a field effect transistor.

17. (Currently amended) A multi-terminal device, comprising:

a substrate comprising a source region, a drain region, and a channel region between said source region and said channel region ~~therebetween~~;

an insulating layer disposed over said channel region, said insulating layer comprising an ~~a layer comprising~~ aluminum nitride layer and a layer comprising at least one of aluminum oxide, silicon dioxide, and silicon nitride ~~disposed over said channel region~~; and

a gate electrode disposed over said insulating layer.

18. (Original) The multi-terminal device of claim 17, wherein said device comprises a field effect transistor.

B1

Claims 19-27. (Currently canceled)